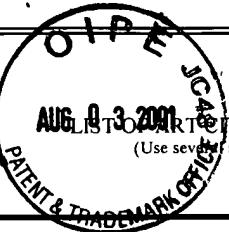
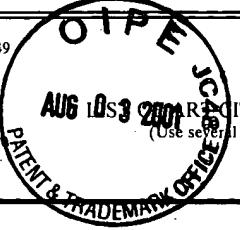
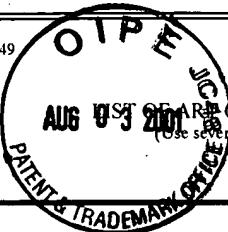


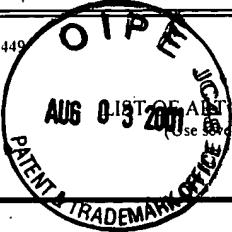
200. Form PTO-1449		U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1035		SERIAL NO. 09/234,233		
LIST OF ARTS CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Weimin Li				
					FILING DATE January 20, 1999		GROUP 2818		
U. S. PATENT DOCUMENTS									
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate	
DV	AA	5,883,011	4/1999	Lin et al		—	—		
	AB	5,677,015	10/1994	Hasegawa		—	—		
	AC	5,783,493	7/1998	Yeh et al		—	—		
	AD	5,807,660	9/1998	Lin et al		—	—		
	AE	4,833,096	5/1989	Huang et al		—	—		
	AF	5,405,489	4/1995	Kim et al		—	—		
	AG	5,470,772	11/1995	Woo		—	—		
	AH	5,652,187	7/1997	Kim et al		—	—		
	AI	5,656,337	8/1997	Park et al		—	—		
	AJ	4,805,683	2/1989	Magdo et al		—	—		
	AK	5,874,367	2/1999	Dobson		—	—		
DV	AL					—	—		
FOREIGN PATENT DOCUMENTS									
		Document Number	Date	Country		Class	Subclass	Translation	
								Yes	No
DV	AM	06067019A	9/1999	Japan (Glass)		—	—		
DV	AN	9750993	2/1997	Japan		—	—		
DV	AO	63-157443A	6/30/1988	Japan (Morita)		—	—		
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)									
DV	AP		TEXT: Jenkins, F. et al., "Fundamentals of Optics", Properties of Light, pp. 9-10. (No date)						
DV	AQ		TEXT: Wolf, S. et al., "Silicon Processing for the VLSI Era", Vol. 1, pp. 437-441. (No date)						
	AR								
EXAMINER	Shuland			DATE CONSIDERED		10/11/01			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1035		SERIAL NO. 09/234,233	
 AUG 9 3 2001 LIST OF ARTICLESITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Weimin Li			
					FILING DATE January 20, 1999		GROUP 2818	
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate
DV	AA	5,585,880	1/1999	Dobson et al				
	AB	5,219,613	6/1993	Fabry et al				
	AC	5,270,267	12/1993	Quellet				
	AD	5,541,445	7/1996	Quellet				
	AE	6,022,404	2/2000	Ettlinger et al				
	AF	5,709,741	1/1998	Akamatsu et al				
	AG	4,648,904	3/1987	Depasquale et al				
	AH	4,158,717	6/1979	Nelson				
	AI	5,667,015	9/1997	Harestad et al				
	AJ	5,661,093	8/1997	Ravi et al				
	AK	5,536,857	7/1996	Naula				
	AL	4,695,859	9/1987	Guha et al				
	AM	4,954,867	6/1990	Hosaka				
	AN	5,441,797	8/1995	Hogan				
	AO	5,710,067	1/1998	Foote				
	AP	5,759,755	6/1998	Park et al				
	AQ	5,838,052	11/1998	McTeer				
V DV	AR	5,883,011	4/1999	Lin et al				
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country		Class	Subclass	Translation
								Yes
								No
DV	AS	406244172A	9/1994	Japan				
DV	AT	593,727	10/1947	GB				
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
EXAMINER <i>Shuland</i>				DATE CONSIDERED <i>10/11/01</i>				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1035		SERIAL NO. 09/234,233		
 AUG 10 1999 2001 CITED BY APPLICANT (Use several sheets if necessary)			APPLICANT Weimin Li						
			FILING DATE January 20, 1999		GROUP 2818				
U.S. PATENT DOCUMENTS									
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate	
DV	AA	5,061,509	10/1991	Naito et al		—	—		
	AB	4,600,671	7/1986	Saitoh et al		—	—		
	AC	5,753,320	5/1998	Mikoshiba et al		—	—		
	AD	5,356,515	10/1994	Tahara et al		—	—		
	AE	5,674,356	10/07/97	Nagayama		—	—		
	AF	5,731,242	03/24/98	Parat et al.		—	—		
	AG	5,741,721	04/21/98	Stevens		—	—		
	AH	5,034,348	07/23/91	Hartwick et al.		—	—		
	AI	5,472,829	12/05/95	Ogawa		—	—		
	AJ	5,641,607	06/24/97	Ogawa et al.		—	—		
DV	AK	5,648,202	07/15/97	Ogawa et al.		—	—		
	AL					—	—		
FOREIGN PATENT DOCUMENTS									
		Document Number	Date	Country		Class	Subclass	Translation	
								Yes	No
DV	AM	5-263255	10/1993	Japan		—	—		
DV	AN	0 471 185 A2	7/10/91	EPO		—	—		
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)									
DV	AO		D.R. McKenzie et al., "New Technology for PACVD", Surface and Coatings Technology, 82 (1996), pp. 326-333.						
DV	AP		S. McClatchie et al.; "Low Dielectric Constant Flowfill® Technology For IMD Applications"; undated; 7 pages						
DV	AQ		K. Beekmann et al.; "Sub-micron Gap Fill and In-Situ Planarisation using Flowfill™ Technology"; October 1995; pp. 1-7						
EXAMINER <i>Shuland</i>				DATE CONSIDERED <i>10/11/01</i>					
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>									

<p>Form PTO-144 AUG 03 2001 LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)</p> <p>U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE</p> <p>PTENT & TRADEMARK OFFICE</p>				ATTY. DOCKET NO. MI22-1035		SERIAL NO. 09/234,233		
				APPLICANT Weimin Li				
				FILING DATE January 20, 1999		GROUP 2818		
				U.S. PATENT DOCUMENTS				
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate
DV	AA	5,670,297	09/23/97	Ogawa et al.				
	AB	5,677,111	10/14/97	Ogawa				
	AC	5,698,352	12/16/97	Ogawa et al.				
	AD	5,831,321	11/03/98	Nagayama				
	AE	5,591,566	01/07/97	Ogawa				
	AF	6,008,124	12/28/99	Sekiguchi et al.				
	AG	5,340,621	08/23/94	Matsumoto et al.				
	AH	5,600,165	02/04/97	Tsukamoto et al.				
	AI	5,872,385	02/16/99	Taft et al.				
	AJ	5,960,289	09/28/99	Tsui et al.				
	AK	5,968,324	10/19/99	Cheung et al.				
DV	AL	6,020,243	02/01/00	Wallace et al.				
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country		Class	Subclass	Translation
DV	AM	0 588 087 A2	8/18/93	EPO				Yes
DV	AN	0 588 087 A3	8/18/93	EPO				No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
DV	AO		A. Kiermasz et al.; "Planarisation for Sub-Micron Devices Utilising a New Chemistry"; Electrotech, February 1995; 2 pages					
DV	AP		IBM Technical Disclosure Bulletin "Low-Temperature Deposition of SiO ₂ , Si ₃ N ₄ or SiO ₂ -Si ₃ N ₄ ," Vol. 28, No. 9, p. 4170, Feb. 1986.					
DV	AQ		ARTICLE: Bencher, C. et al., "Dielectric antireflective coatings for DUV lithography", Solid State Technology (March 1997), pp.109-114.					
EXAMINER <i>Gruland</i>				DATE CONSIDERED <i>10/11/01</i>				
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1035		SERIAL NO. 09/234,233	
 AUG 9 2001 CITED BY APPLICANT <small>(use several sheets if necessary)</small>					APPLICANT Weimin Li			
					FILING DATE January 20, 1999		GROUP 2818	
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate
DV	AA	6,054,379	04/25/00	Yau et al.		—	—	
	AB	5,948,482	09/07/99	Brinker et al.		—	—	
	AC	5,800,877	09/01/98	Maeda et al.		—	—	
	AD	5,260,600	11/09/93	Harada		—	—	
	AE	4,992,306	02/12/91	Hochberg et al.		—	—	
	AF	4,702,936	10/27/87	Maeda et al.		—	—	
	AG	4,863,755	09/05/89	Hess et al.		—	—	
	AH	5,234,869	08/10/93	Mikata et al.		—	—	
	AI	5,302,366	04/12/94	Schuette et al.		—	—	
	AJ	5,591,494	01/07/97	Sato et al.		—	—	
	AK	5,968,611	10/19/99	Kaloyerous et al.		—	—	
	AL	6,159,871	12/12/00	Loboda et al.		—	—	
	AM	5,744,399	4/1998	Rostoker		—	—	
	AN	5,883,014	3/1999	Chen		—	—	
DV	AO	6,017,779	1/25/00	Miyasaka		—	—	
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country		Class	Subclass	Translation
								Yes No
DV	AP	09055351	25/2/97	Japan		—	—	
DV	AQ	0 778 496 A2	05/12/96	EPO		—	—	
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
DV	AR		Noboru Shibata, "Plasma-Chemical Vapor-Deposited Silicon Oxide/Silicon Oxynitride Double-Layer Antireflective Coating for Solar Cells", Japanese Journal of Applied Physics, Vol. 30, No. 5, May 1991, pp. 997-1001.					
DV	AS		Julius Grant, Hackh's Chemical Dictionary, Fourth Edition, McGraw-Hill Book Company, © 1969, rented by Grant © 1972, pp. 27					
EXAMINER <i>Shuland</i>				DATE CONSIDERED <i>10/11/01</i>				
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1035	SERIAL NO. 09/234,233			
 LIST OF ARTS CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Weimin Li				
				FILING DATE January 20, 1999	GROUP 2818			
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
DV	AA	5,472,827	12/1995	Ogawa et al.				
	AB	6,156,674	12/5/00	Li et al				
	AC	6,461,003	10/24/95	Haveman				
	AD	6,124,641	9/26/00	Matsura				
	AE	5,554,567	9/10/96	Wang				
DV	AF	6,028,015	2/22/00	Wang				
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
DV	AG	EP 0 464 515 A3/B1	08.01.92	EPO (Mikata et al.)				
DV	AH	EP 0 771 886 A1	07.05.97	EPO (Loboda)				
DV	AI	20029	US99	Search Report				
DV	AJ	20030	US99	Search Report				
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
DV	AK	Ralls, Kenneth M., "Introduction to Materials Science and Engineering", John Wiley & Sons, © 1976, pp. 312-313						
DV	AL	Ravi K. Laxman, "Synthesizing Low-k CVD Materials for Fab Use", Semiconductor International, Nov. 2000, 10 pps.						
DV	AM	Anonymous, "New gas helps make faster IC's, Machine Design Cleveland, © Penton Media, Inc., November 4, 1999, pp. 118						
DV	AN	Loboda et al, "Using Trimethylsilane to Improve Safety Throughput and Versatility in PECVD Processes", 4th International Symposium on Silicon Nitride and Silicon Dioxide Thin Insulating Films, The Electrochemical Society, Abstract No. 358, p. 454, May 1997.						
DV	AO	ARTICLE: Bencher, C. et al., "Dielectric antireflective coatings for DUV lithography", Solid State Technology (March 1997), pp. 109-114.						
DV	AP	ARTICLE: Dammel, R. R. et al., "Dependence of Optical Constants of AZ® BARLi™ Bottom Coating on Back Conditions", SPIE Vol. 3049 (1997), pp. 963-973.						
DV	AQ	TEXT: Heavens, O. S., "Optical Properties of Thin Solid Films", pp. 48-49.						
EXAMINER <i>gvaland</i>			DATE CONSIDERED <i>10/11/01</i>					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1035	SERIAL NO. 09/234,233
 LIST OF ARTS CITED BY APPLICANT <small>(Use reverse sheets if necessary)</small>				APPLICANT Weimin Li	
				FILING DATE January 20, 1999	GROUP 2818
U.S. PATENT DOCUMENTS					
*Examiner Initial		Document Number	Date	Name	Class
DV	AA	09/146,842	9/3/98	Yin et al	
DV	AB	09/146,843	9/3/98	Li et al	
DV	AC	09/030,618	2/25/98	Holscher et al	
	AD				
	AE				
	AF				
	AG				
	AH				
	AI				
	AJ				
	AK				
	AL				
FOREIGN PATENT DOCUMENTS					
		Document Number	Date	Country	Class
					Subclass
					Translation
					Yes
					No
	AM				
	AN				
	AO				
	AP				
	AQ				
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)					
	AR				
	AS				
EXAMINER	Sundland		DATE CONSIDERED	10/11/01	
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>					

LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)APPLICANT
Weimin Li et al.FILING DATE
Filed herewithGROUP
Unknown

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
DV	AA	4,474,975	10/84	Clemons et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

DV	AO		M. Matsuura et al.; "A Highly Reliable Self-planarizing Low-k Intermetal Dielectric for Sub-quarter Micron Interconnects"; July 1997;				
		pp. 31.6.1-31.6.4					
DV	AP		O. Horie et al.; "Kinetics and Mechanism of the Reactions of O(P) with SiH_4 , CH_3SiH_3 , $(CH_3)_2SiH_2$, and $(CH_3)_3SiH$ "; The Journal of Physical Chemistry, Vol. 95, No. 11, 1991; pp. 4393-4400				
		Chemistry, Vol. 95, No. 11, 1991; pp. 4393-4400					
DV	AQ		Robert Withmire et al.; "Matrix Reactions of Methyisilanes and Oxygen Atoms"; The Journal of Physical Chemistry, Vol. 92, No. 3, 1988;				
		pp. 594-602					
DV	AR		Ajey M. Joshi et al.; "Plasma Deposited Organosilicon Hydride Network Polymers as Versatile Resists for Entirely Dry Mid-Deep UV Photolithography"; SPIE Vol. 1925, 1993; pp. 709-720				
		Photolithography"; SPIE Vol. 1925, 1993; pp. 709-720					

EXAMINER DV

DATE CONSIDERED 07/07/00

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

EL169865225

200 FORM PTO-1035		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1035	SERIAL NO. 09/234,233
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Weimin Li	
				FILING DATE January 20, 1999	GROUP 2818

U.S. PATENT DOCUMENTS						
*Examiner Initial		Document Number	Date	Name	Class	Subclass
DV	AA	5,314,724	05/1994	Tsukane et al		
	AB	5,376,591	12-94 10/1998	Yamaseki et al Maeda et. al.		
	AC	6,001,741	12/1999	Alers		
	AD	6,072,227	06/2000	Yau et al		
↓	AE	5,786,039	7/1998	Brouquet		
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					
	AL					

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AM							
	AN							
	AO							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AP							
	AQ							
	AR							

EXAMINER *Shuland*DATE CONSIDERED *10/11/01*

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered.
Include copy of this form with next communication to applicant.

200 Form PTO-1

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MI22-1035SERIAL NO.
09/234,233LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)APPLICANT
Weimin LiFILING DATE
January 20, 1999GROUP
2818

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
DV	AA	5,314,724	05/1994	Tsukane et al			
	AB	5,376,591	10/1998	Yamazaki et al			
	AC	6,001,741	12/1999	Alers			
	AD	6,072,227	06/2000	Yau et al			
↓	AE	5,786,039	7/1998	Brouquet			
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AM							
	AN							
	AO							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AP		
	AQ		
	AR		

EXAMINER *Shuland*

DATE CONSIDERED

10/11/01

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered.
Include copy of this form with next communication to applicant.

E1844048247